

ABSTRACT

This semiconductor device (100A) includes: a substrate (1); a gate electrode (3) and a first transparent electrode (2) which are formed on the substrate (1); a first insulating layer (4) formed over the gate electrode (3) and the first transparent electrode (2); an oxide semiconductor layer (5) formed on the first insulating layer (4); source and drain electrodes (6s, 6d) electrically connected to the oxide semiconductor layer (5); and a second transparent electrode (7) electrically connected to the drain electrode (6d). At least a portion of the first transparent electrode (2) overlaps with the second transparent electrode (7) with the first insulating layer (4) interposed between them, and the oxide semiconductor layer (5) and the second transparent electrode (7) are formed out of the same oxide film.